



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#8/a
7/15/02
Hornet

In re the Application of: **TAKEMORI, Toshiyuki et al.**

Group Art Unit: **2814**

Serial No.: **09/660,439**

Examiner: **Steven H. RAO**

Filed: **September 12, 2000**

For: **TRANSISTOR AND METHOD OF MANUFACTURING THE SAME**

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TECHNOLOGY CENTER 2800

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

July 5, 2002

Sir:

In response to the Office Action dated **April 4, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

Claims 1, 2, 6, 7, 10 and 11 have been amended so as to read as follows:

1. (Amended) A transistor comprising;

a semiconductor substrate having a semiconductor layer, a drain layer of a first conductivity type provided on said semiconductor layer and a conductive region of a second conductivity type formed by diffusing an impurity of the second conductivity type from a surface of said drain layer;)
a trench provided such that it extends from a surface of said conductive region to said drain

AC1

Initials
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